

ABSTRACT

A NOVEL WAY TO FABRICATE THE SELF-ALIGNED T-SHAPE GATE TO REDUCE GATE RESISTIVITY

Disclosed is a method of fabricating a semiconductor field effect transistor, wherein the gate has a short foot portion in contact with the semiconductor substrate for a short gate length and consequent low capacitance, and a large amount of metal in a contact portion for low gate resistance. Salicides are formed on the T-gate source on drain contact areas resulting in large, low resistance contact areas.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)